

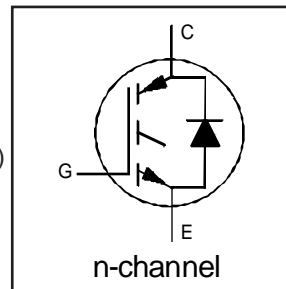
# IRGPC20KD2

INSULATED GATE BIPOLAR TRANSISTOR  
WITH ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated  
UltraFast CoPack IGBT

## Features

- Short circuit rated -10 $\mu$ s @125°C,  $V_{GE} = 15V$
- Switching-loss rating includes all "tail" losses
- HEXFRED™ soft ultrafast diodes
- Optimized for high operating frequency (over 5kHz)  
See Fig. 1 for Current vs. Frequency curve



$V_{CES} = 600V$

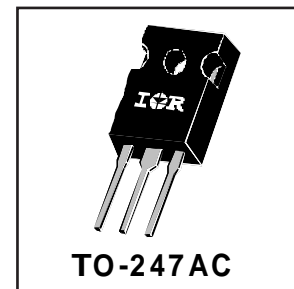
$V_{CE(sat)} \leq 3.5V$

@  $V_{GE} = 15V, I_C = 6.0A$

## Description

Co-packaged IGBTs are a natural extension of International Rectifier's well known IGBT line. They provide the convenience of an IGBT and an ultrafast recovery diode in one package, resulting in substantial benefits to a host of high-voltage, high-current, applications.

These new short circuit rated devices are especially suited for motor control and other applications requiring short circuit withstand capability.



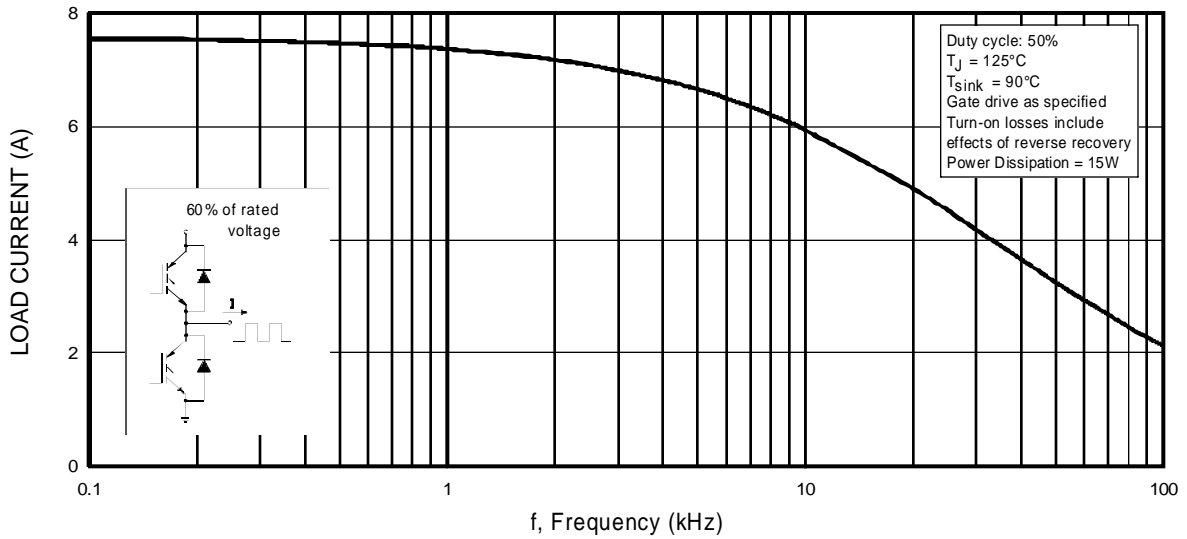
## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	10	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	6.0	
$I_{CM}$	Pulsed Collector Current ①	20	
$I_{LM}$	Clamped Inductive Load Current ②	20	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	7.0	
$I_{FM}$	Diode Maximum Forward Current	20	
$t_{sc}$	Short Circuit Withstand Time	10	$\mu s$
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
$T_J$	Operating Junction and	-55 to +150	$^\circ C$
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

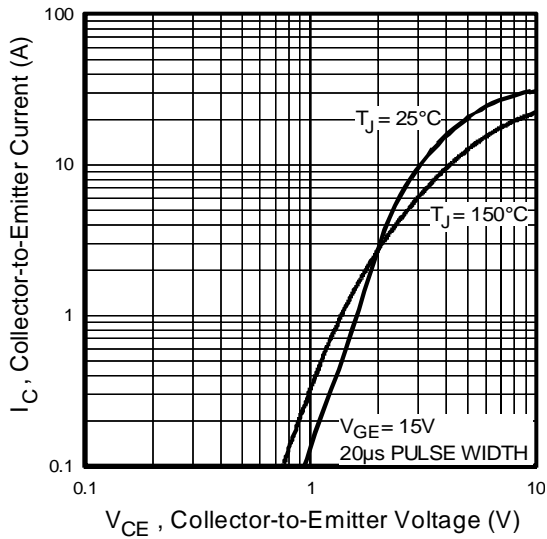
## Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	-----	-----	2.1	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	-----	-----	3.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	-----	0.24	-----	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	-----	-----	40	
Wt	Weight	-----	6 (0.21)	-----	g (oz)

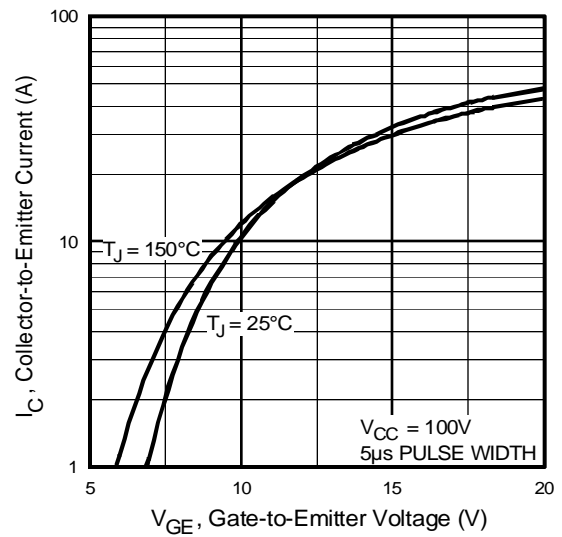




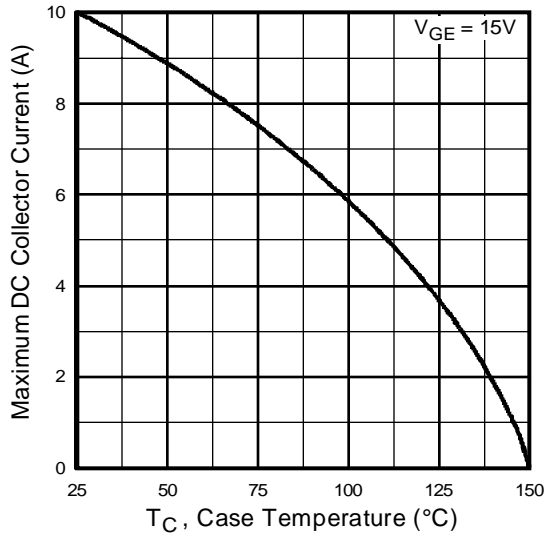
**Fig. 1 - Typical Load Current vs. Frequency**  
(Load Current =  $I_{RMS}$  of fundamental)



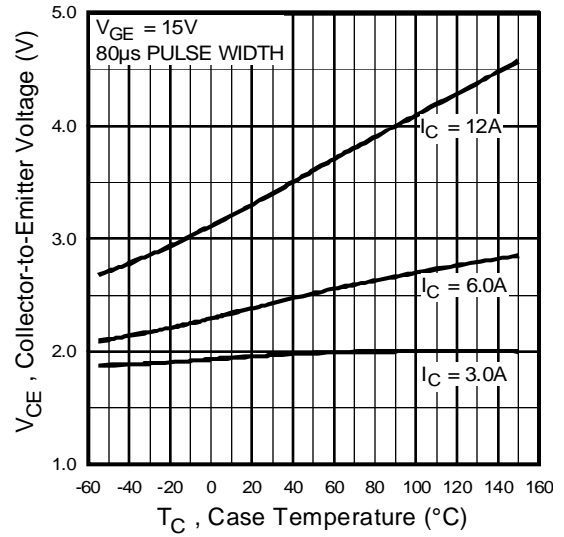
**Fig. 2 - Typical Output Characteristics**



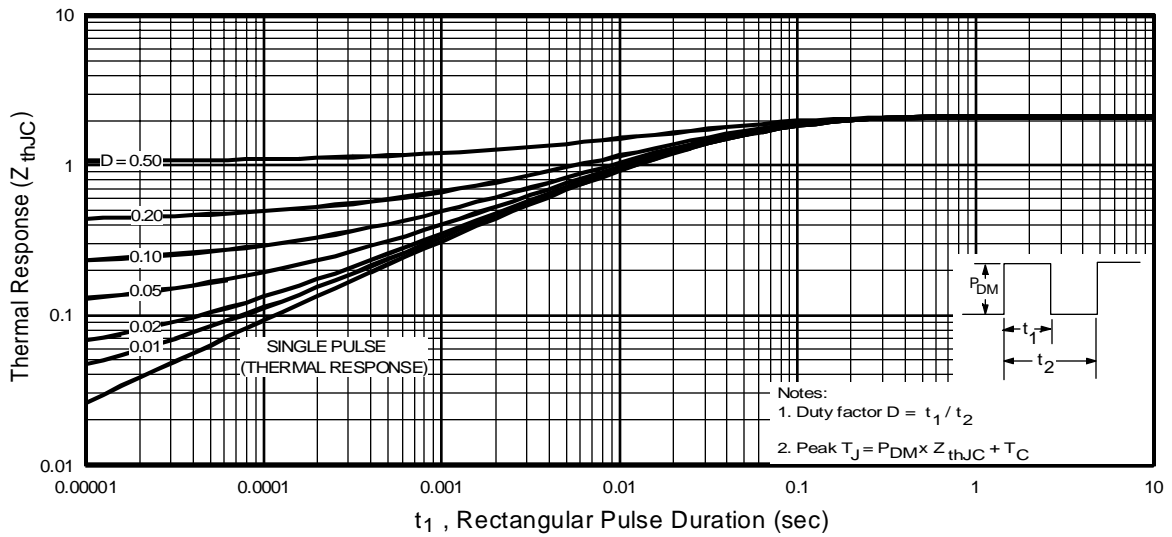
**Fig. 3 - Typical Transfer Characteristics**



**Fig. 4** - Maximum Collector Current vs. Case Temperature



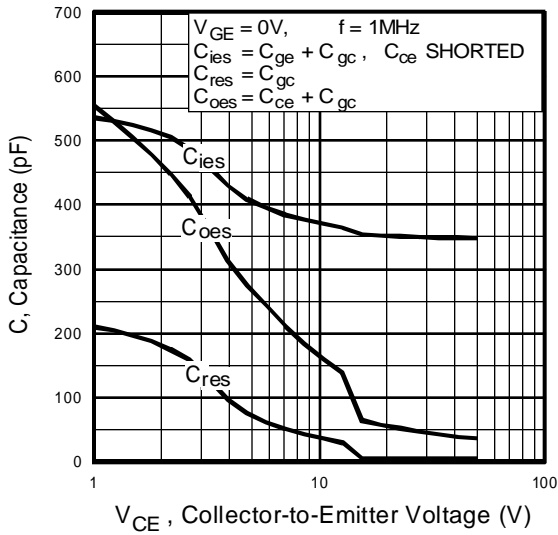
**Fig. 5** - Collector-to-Emitter Voltage vs. Case Temperature



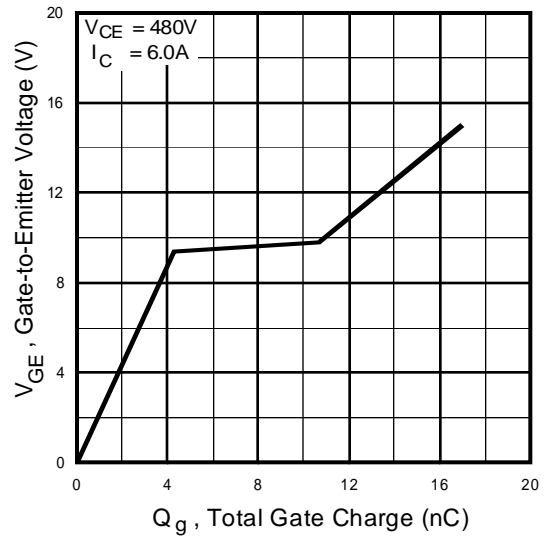
**Fig. 6** - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case



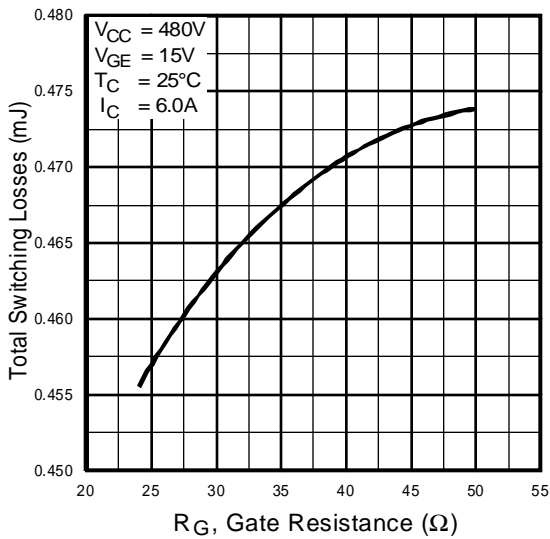
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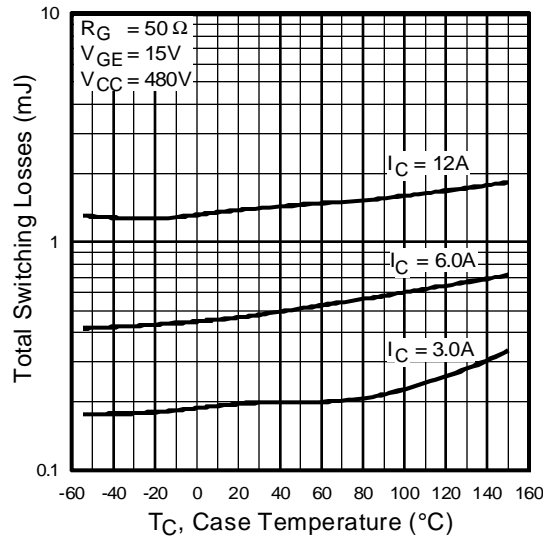
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



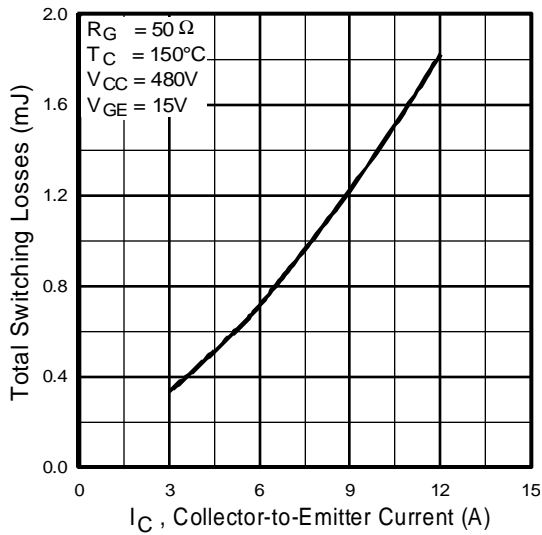
**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage



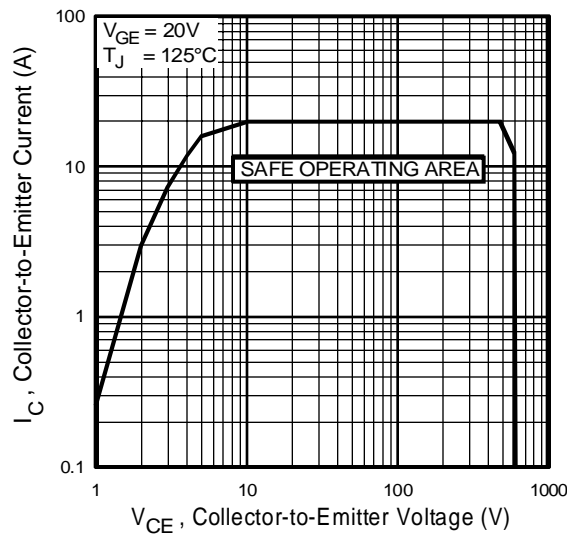
**Fig. 9** - Typical Switching Losses vs. Gate Resistance



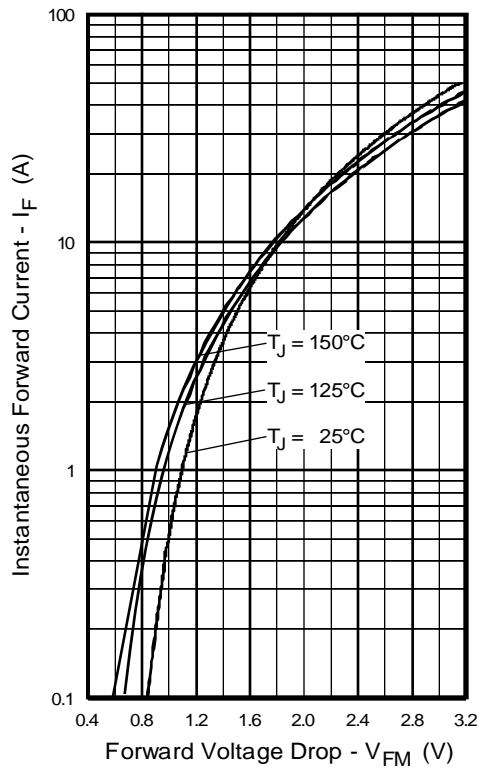
**Fig. 10** - Typical Switching Losses vs. Case Temperature



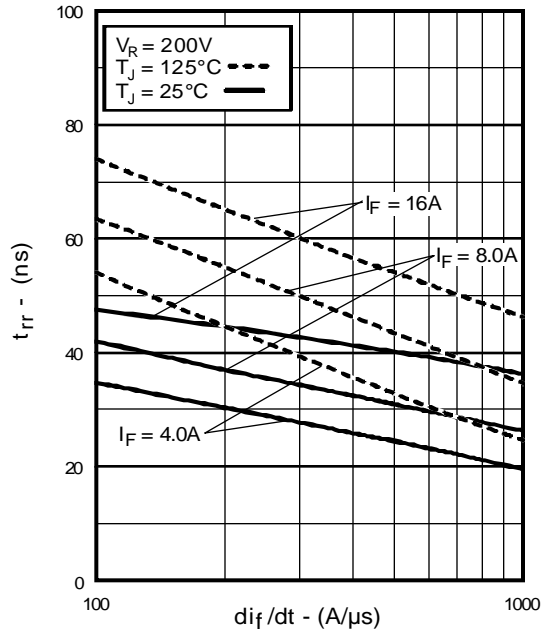
**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



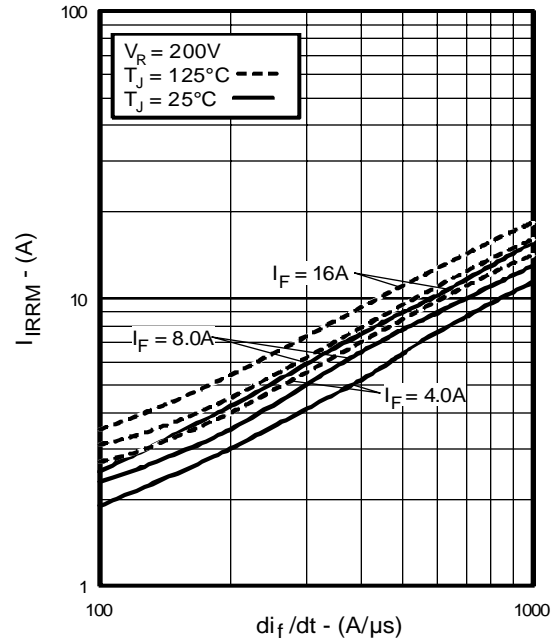
**Fig. 12** - Turn-Off SOA



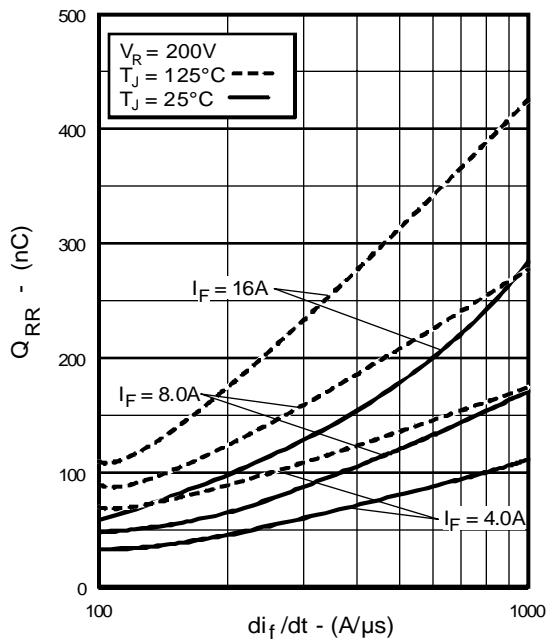
**Fig. 13** - Maximum Forward Voltage Drop vs. Instantaneous Forward Current



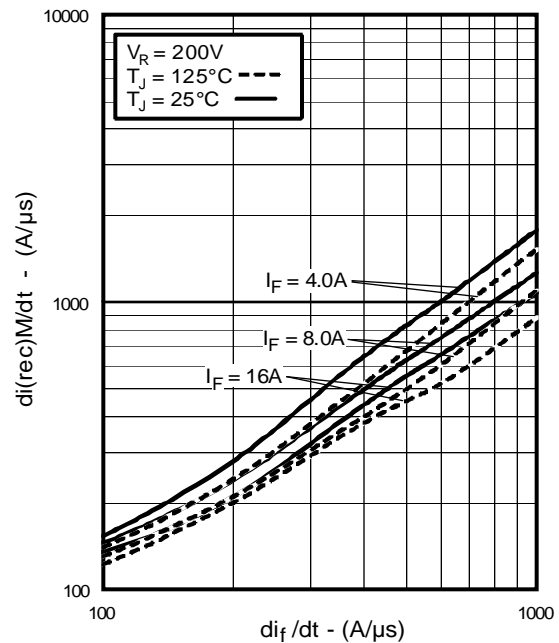
**Fig. 14** - Typical Reverse Recovery vs.  $di_f/dt$



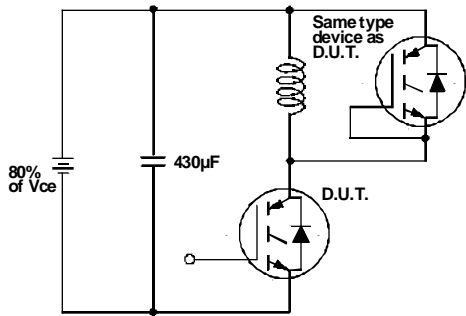
**Fig. 15** - Typical Recovery Current vs.  $di_f/dt$



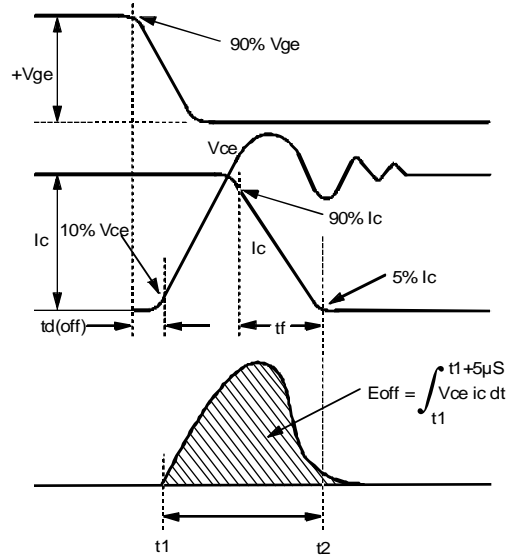
**Fig. 16** - Typical Stored Charge vs.  $di_f/dt$



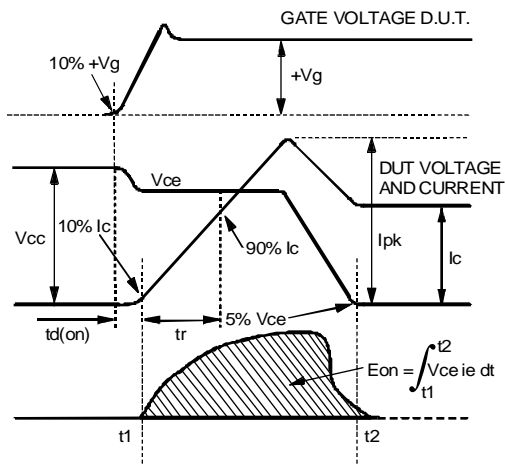
**Fig. 17** - Typical  $di_{(rec)M}/dt$  vs.  $di_f/dt$



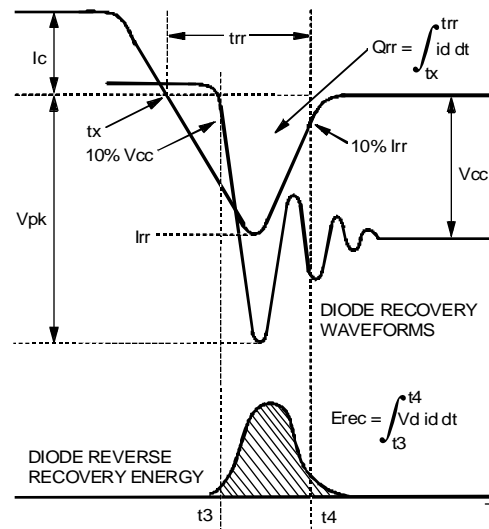
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}(\text{diode})$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



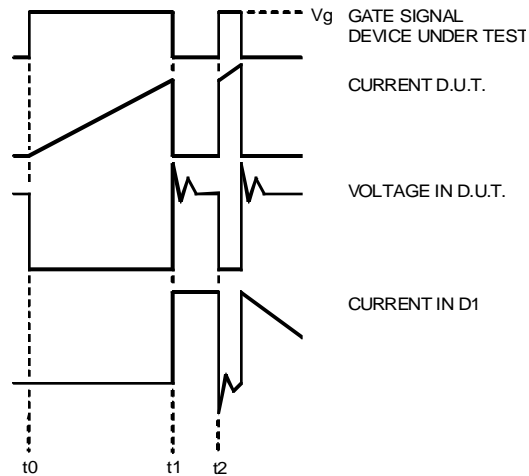
**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



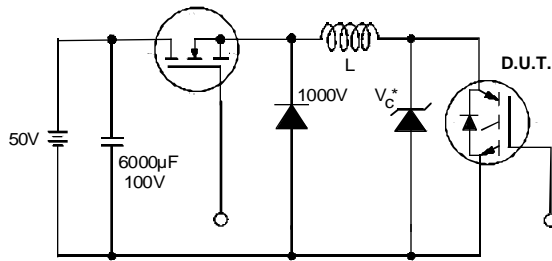
**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$



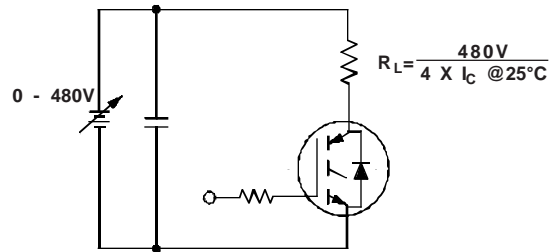
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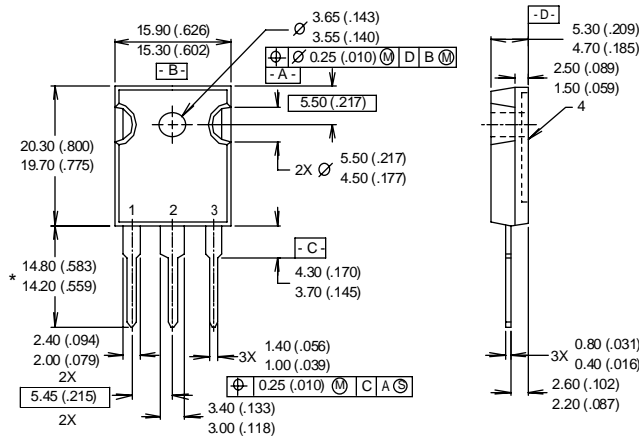
**Fig. 18e - Macro Waveforms for Test Circuit of Fig. 18a**



**Fig. 19 - Clamped Inductive Load Test Circuit**



**Fig. 20 - Pulsed Collector Current Test Circuit**



- NOTES:
- 1 DIMENSIONS & TOLERANCING PER ANSI Y14.5M, 1982.
  - 2 CONTROLLING DIMENSION : INCH.
  - 3 DIMENSIONS ARE SHOWN MILLIMETERS (INCHES).
  - 4 CONFORMS TO JEDEC OUTLINE TO-247AC.

- LEAD ASSIGNMENTS
- 1 - GATE
  - 2 - COLLECTOR
  - 3 - EMITTER
  - 4 - COLLECTOR

\* LONGER LEAD (2.0mm) VERSION AVAILABLE (TO-247AD) TO ORDER ADD "E" SUFFIX TO PART NUMBER

CONFORMS TO JEDEC OUTLINE TO-247AC (TO-3P)  
Dimensions in Millimeters and (Inches)



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